

**A CHEMICAL MECHANICAL POLISHING SLURRY
COMPOSITION FOR POLISHING CONDUCTIVE AND NON-
CONDUCTIVE LAYERS ON SEMICONDUCTOR WAFERS**

ABSTRACT OF THE INVENTION

A novel CMP slurry composition used for polishing metals, the composition comprising: a dispersion solution comprising an abrasive. The slurry composition has a large particle count of about 25 to about 150,000 particles having a particle size greater than 0.5 μm in 30 μL of slurry, which is achieved by filtering the slurry composition prior to use. Also, the inclusion of a chemical activity enhancer, such as, an amine and a corrosion inhibitor, results in the appropriate copper removal rate without increasing static etch rates.